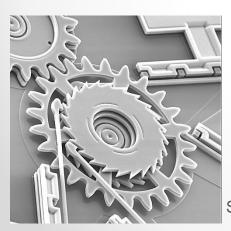
Sensors and Actuators (เซนเซอร์และตัวขับเร้า) <sub>Chapter 2: BIO(CHEMICAL) SENSORS</sub>

By

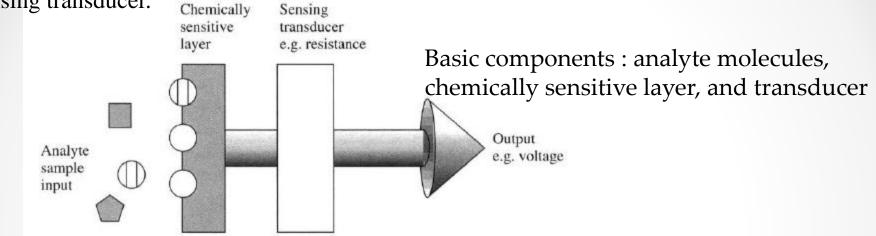


Dr.Santhad Chuwongin office : 405 Tue, Fri : 8-9 am, 1-4 pm

2018

# **BIO(CHEMICAL) SENSORS**

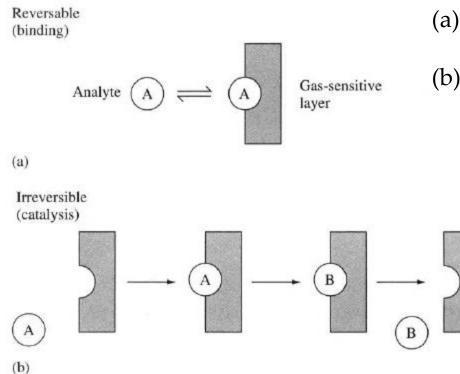
The basic components of these sensor comprise a chemically sensitive layer interfaced to a sensing transducer.



 $\succ$  The analyte molecules interact with the chemically sensitive layer and produce a physical change that is detected by the transducer and are converted into an electrical output signal.

The nature of this interaction is determined by the type of material used and can be either a reversible process or an irreversible reaction

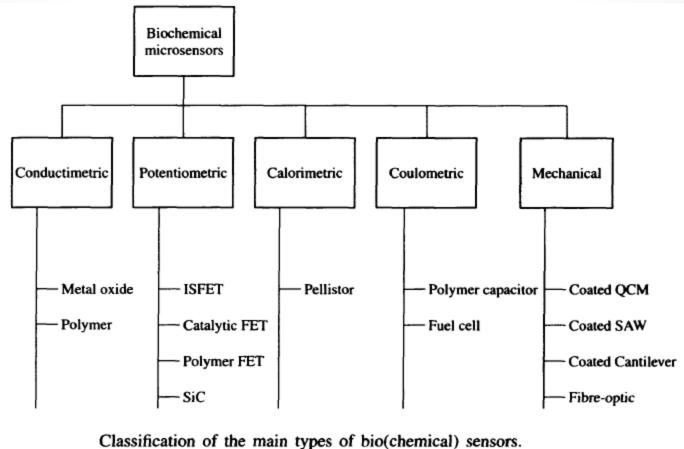
## **BIO(CHEMICAL) SENSORS**



(a) reversible binding of the analyte A to a site at the chemically sensitive layer(b) irreversible reaction of the analyte A at a site to produce molecule B at the chemically sensitive layer.

## **BIO(CHEMICAL) SENSORS**

The signals that are measured can be the change in electrical resistance (i.e. conductimetric), change in work function (i.e. potentiometric), change in the heat of reaction (i.e. calorimetric), and so on.

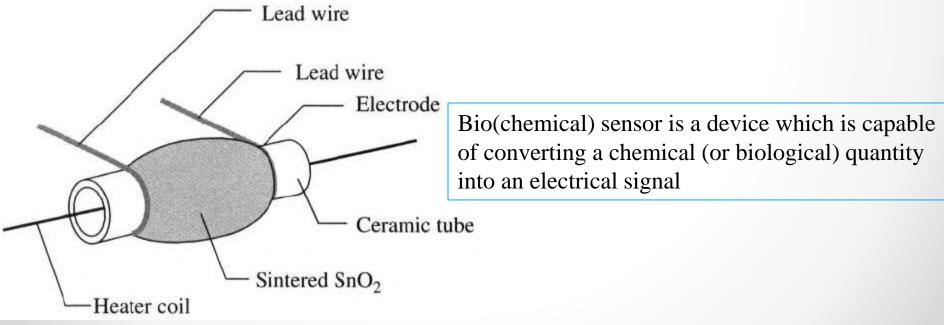


Devices listed are those that can be regarded as microsensors

≻Conductimetric gas sensors are based on the principle of measuring a change in the electrical resistance of a material upon the introduction of the target gas.

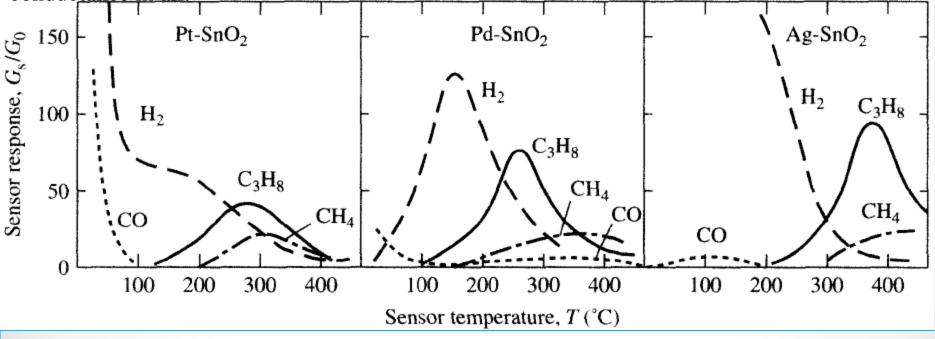
The most common type of gas sensor employs a solid-state material as the gas-sensitive element. The principal class of material used today is emiconducting metal oxides, with tin oxide  $(SnO_2)$  being the most popular.

 $\succ$  The device consists of a wire-wound platinum heater coil inside a ceramic former onto which a thick layer of porous tin oxide is painted manually.



#### CONDUCTIMETRIC SENSORS (Selectivity Enhancement by Doping)

Tin oxide devices are operated at various high temperatures and doped with different materials to enhance their specificity. The response of a tin oxide sensor, in terms of its relative conductance  $G_s/G_0$ , where  $G_s$  is the conductance of a gas of fixed concentration and  $G_0$  is the conductance in air.



Variation of the response of three doped tin oxide gas sensors with temperature for four different gases.

$$\frac{1}{2}mO_2 + \{\text{vacancy}\} + e^- \longleftrightarrow^{k_1} \{O_m^-\}$$

>vacant sites within the tin oxide lattice react with atmospheric oxygen to abstract electrons out of the conduction band of the tin oxide creating chemisorbed oxygen sites such as  $O^{-}$ ,  $O_2$ .

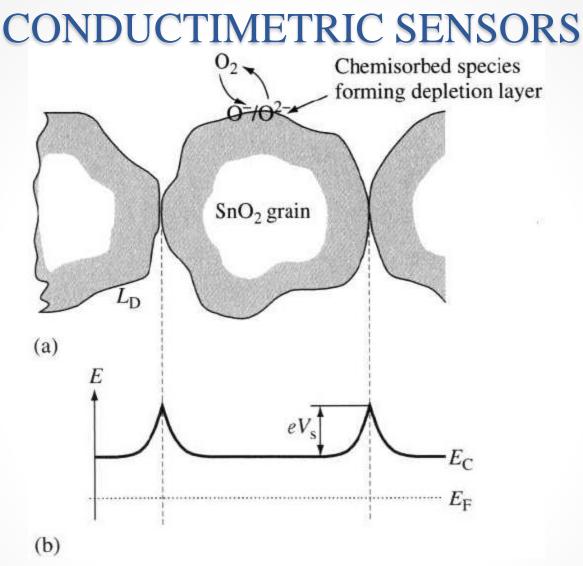
reversible reaction is disturbed when the analyte molecule X reacts with the chemisorbed oxygen species  $k_2$ 

$$X + \{O_m^-\} \xrightarrow{\kappa_2} \{XO_m\} + e^-$$

$$\Delta \sigma = \mu_n e \Delta n$$

 $\Delta G \propto \frac{k_1}{k_2} C^r$ 

This change in device conductance can be approximately related to the gas concentration C from the chemical rate constants  $k_1$  and  $k_2$  defined in Equations ,where the exponent r has a value that lies between 0.5 and 0.9 and depends on the kinetics of the reaction



(a) Schematic diagram showing a series of nanometre-sized grains in a sintered tin oxide film and(b) band diagram showing the effect of the oxygen-induced depletion regions.

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>lists some tin oxide gas sensors that are commercially available together with their properties.

Some commercial gas sensors cased on semiconadoung metal onde						
Manufacturer	Model	Material	Measurand	Range (PPM)	(Power mW)	Cost <sup>a</sup> (euro)
Figaro Inc. (Japan)	TGS842	Doped SnO <sub>2</sub>	Methane	500-10000	835	13
Figaro Inc. (Japan)	TGS825	Doped SnO <sub>2</sub>	Hydrogen sulfide	5-100	660	50
Figaro Inc. (Japan)	TGS800	Doped SnO <sub>2</sub>	Air quality (smoke)	<10	660	13
FiS (Japan)	SB5000	Doped SnO <sub>2</sub>	Toxic gas - CO	10-1000	120	13
FiS (Japan)	SP1100	Doped SnO <sub>2</sub>	Hydrocarbons	10-1000	400	15
Capteur <sup>b</sup> (UK)	LGS09	Undoped oxide	Chlorine	0-5	650	25
Capteur (UK)	LGS21	Undoped oxide	Ozone	0-0.3	800	25

Some commercial gas sensors based on semiconducting metal oxide

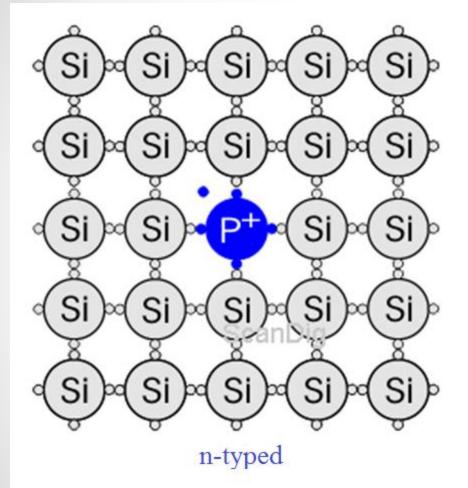
The requirement to run this type of gas sensor at a high temperature causes the power consumption of about 0.8 W of a Taguchi-type device to be a problem for handheld units.

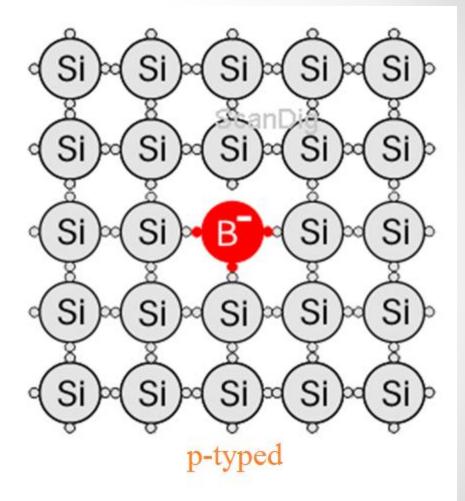
Semiconducting metal oxides (SnO2, ZnO, Fe2O3) are commonly used (e.g., SnO2 for CO, alcohol, H2, H2S, ...etc)

- ➤ The increase and decrease of resistance affected by: Adsorption of O2 on surface: O2 + 2e- (due to vacant sites in SiO2) → 2O- (then R increases) Reaction with combustible gases H2: H2 + O- → H2O + e- (then R decreases)
- The devices are operated at high temperatures (typ. 300 400 °C) Speed up the chemical reaction Ameliorate the humidity effect Consume a few hundred mW

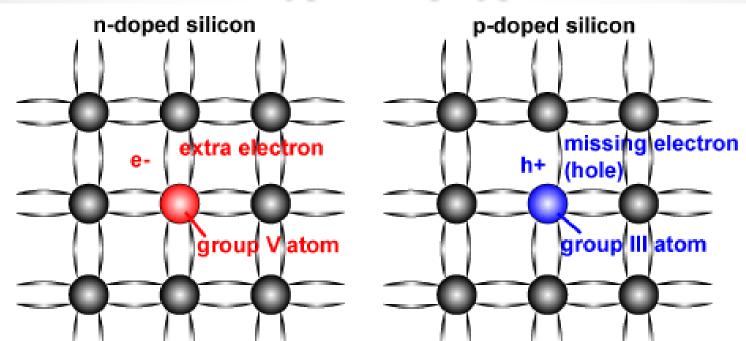


### n-type and p-type





#### n-type and p-type



Schematic of a silicon crystal lattice doped with impurities to produce *n*-type and *p*-type semiconductor material.

	N-type (negative)	P-type (positive)
Dopant	Group V (e.g. Phosphorous)	Group III (e.g. Boron)
Bonds	Excess Electrons	Missing Electrons (Holes)
Majority Carriers	Electrons	Hole
Minority Carriers	Holes	Electrons